

160 μ W, High-Slew Smartwatch LCD Driver

EE 140 Final Project Presentation

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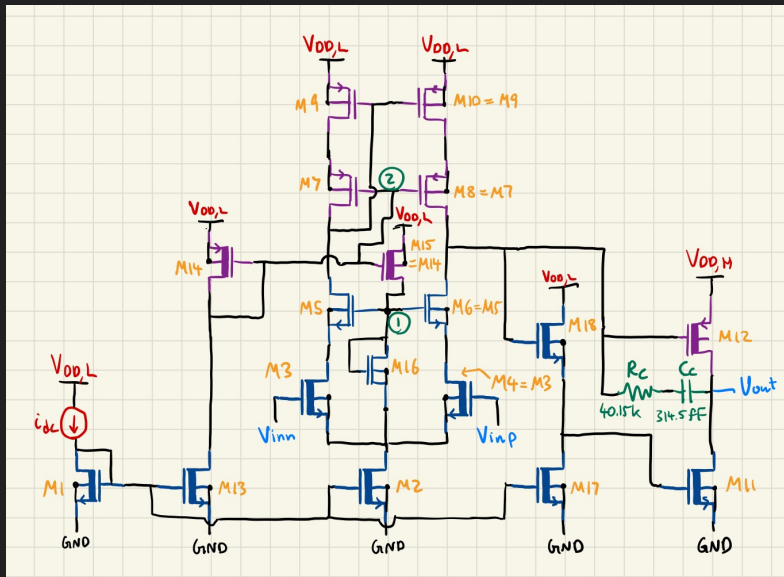
Introduction

Comparison with Target Specifications

Property	Specification	Achieved
Power Supplies	$\leq 1.8V$, GND	1.8V, 1.62V, GND
Closed Loop DC Gain	2	2
Load	800 Ω , 30pF	same
Max. Settling Time	180.22ns	178.57ns
Total Error	0.2%	0.013%
Power Consumption	$\leq 750\mu W$	159.24 μW
Output Voltage Swing	≥ 1.4	≥ 1.4
Max. Mirror Ratio	20	18
Max. Added Capacitance	25pF	75fF
CMRR at DC	$\geq 60dB$	87.03dB
PSRR at DC	$\geq 50dB$	59.498dB
Phase Margin	$\geq 45^\circ$	56.16 $^\circ$
FOM	≥ 7.403	35.17

Motivation for Choosing Topologies

Diagram of Circuit (values have since changed)



Stage 1 Considerations

- 1 **High Gain**; meet static error and allow greater proportion of 0.2% to go to dynamic, transient error.
- 2 **Slew Rate**: current drives a small capacitance (compensation) and stage has a somewhat small output swing (second stage applies gain to signal).
- 3 Standard Differential Amplifier doesn't provide enough gain; *need to cascode* \implies telescopic cascode is a valid option.

Stage 2 Considerations

- 1 **Large Output swing**; ensure $V_{ds,sat}$ of devices isn't greater than 200mV.
- 2 **Slew Rate**; Driving large (30pF) load (and also smaller compensation capacitor); need enough current to do so.
- 3 *gain isn't as significant* (if first stage is designed well).

Compensation

- 1 Transient:** with more compensation (higher C , higher R), generally, stage 1 performs worse but stage 2 performs better (but can tune to benefit both!). Amount of compensation determined by which stage is failing the settling time.
- 2 Phase Margin:** miller RC compensation (which I used) can improve phase margin and increase unity-gain frequency (bandwidth).

Design Approach and Techniques

Stage 1: Sizing Devices

- 1 Extensive Matlab $\frac{g_m}{I_D}$ analysis to find the point of maximizing *gain per unit current*.
- 2 System-level analysis yielded range of viable/optimal g_{m1}, r_{o1} values to aim for. Initially, I constrained myself to precise values; later, relaxed constraints to form bias \pm threshold.
- 3 Higher values of $\frac{g_m}{I_D}$ selected (but not so high that J_D drops precipitously, requiring very large W).

Stage 1: Biasing

- 1 Used current mirror network with low current ($2\mu\text{A}$) to set up DC node voltages for NMOS/PMOS sides of cascode. Inspired by homework problem.
- 2 Matlab `look_up` function for a given set of device parameters is more accurate with raw V_{GS}, V_{DS} values than for arbitrary cross-ratios (such as $\frac{g_{ds}}{I_D}$ given a specific $\frac{g_m}{I_D}$).
- 3 Alter bias voltages as needed to make g_{ds} as similar as possible in a given cascode stack ($8\mu\text{S}, 8\mu\text{S}$ better than $11\mu\text{S}, 5\mu\text{S}$).

Stage 1: Impacts of Variables

- 1 Higher length leads to minimal change in power consumption, large increase in gain, and slower settling response.
 - But, can tune to ideal state where improvement in static error outweighs generally slower settling response (for me, 480nm).
- 2 Input common-mode voltage: minimum; large enough to keep devices in saturation, optimal; make g_{ds} of input devices collectively low.
- 3 Use widths to control $V_{ds, sat}$ (pick devices where g_m value matters less, like top stage 1 PMOS devices).

Stage 2: Sizing Devices

- 1 Matlab analysis yet again (started with class A common source, which was very similar to labs).
- 2 Matlab "optimal" sizes would often lead to output bias voltage $\neq 900\text{mV}$; needed to tune widths in Cadence. Sometimes had to compromise; tuning PMOS \implies different $g_{m,p}$ than planned. tuning NMOS \implies different bias current than planned (for class A).

Stage 2: Current/Length Selection

- 1 Selected length based on system-level estimate for f_U (larger lengths may violate unity-gain frequency requirement). Higher lengths led to higher gain.
- 2 Class A Common Source output stage: $g_{m,n}$ doesn't impact performance much (NMOS is there to set a branch bias current).
Class AB stage: $g_{m,\text{eff}} = g_{m,n} + g_{m,p}$ (two signal paths) so both devices matter.
- 3 Wider devices consume more power (more current). Want minimally sized widths that provide enough current to settle within 180ns.

Stage 2: Why a Source-Follower?

- 1 Effective DC level-shifter
- 2 Simple to bias and integrate into a class A common source approach (which I had before). Can bias with generally low current ($\leq 3\mu\text{A}$), and use relative widths to set V_{GS} of NMOS device.
- 3 Overcome slew-rate limit that makes class A very power-hungry + take advantage of increased $g_{m,eff}$.

Compensation

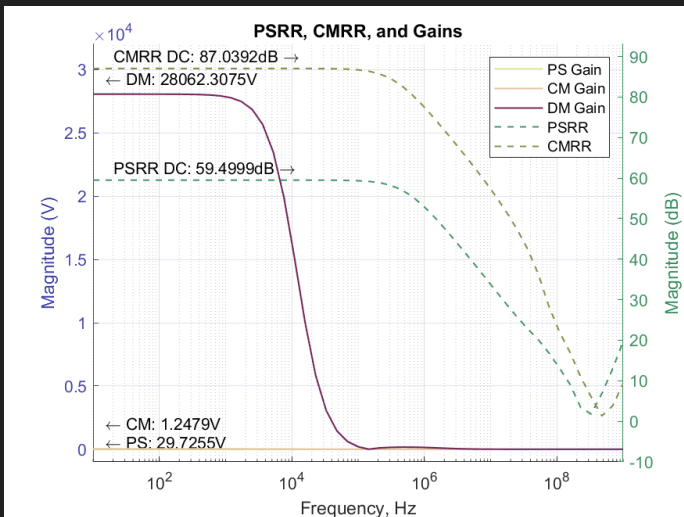
- 1 Matlab can't predict slew-rate limitations; led to more reliance on Cadence testing and parameterized sweeps.
- 2 For a given design, once the DC bias points were tuned, then I honed in on the optimal compensation with 3-4 parametric analyses on C_C, R_C .
- 3 These had minimal impact on power ($\leq 1\mu\text{W}$), didn't change bias points (compensation tuning done last for any given design).
 - In later stages of project, testing the response of a candidate design at a few compensation levels would indicate quickly if the approach was worth pursuing or not (to meet setting time).

Some Other Thoughts

- 1 Optimizing for power is far more rewarding (FOM-wise) than optimizing for settling time. My Matlab analysis indicated that approximate optimal settling time is 85 – 90ns, only half of 180ns (and requires massive power).
- 2 Matlab matches Cadence only to an extent (especially transient response).

Performance Verification

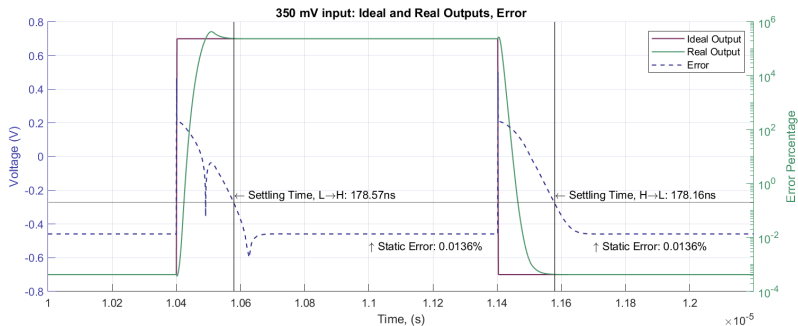
Plot of Values



ADE Output (Confirmation of Plot Values)

Outputs			
	Name/Signal/Expr	Value	Plot
1	cm_gain	wave	<input checked="" type="checkbox"/>
2	dm_gain	wave	<input checked="" type="checkbox"/>
3	CMRR	87.0356	<input checked="" type="checkbox"/>
4	CMRR_freq	wave	<input checked="" type="checkbox"/>
5	ps_gain	wave	<input checked="" type="checkbox"/>
6	PSRR_freq	wave	<input checked="" type="checkbox"/>
7	PSRR	59.4983	<input checked="" type="checkbox"/>
8	Phase Margin	56.1613	<input checked="" type="checkbox"/>
9	Phase Margin Frequency	31.1979M	<input checked="" type="checkbox"/>
10	Loop Gain Phase	wave	<input checked="" type="checkbox"/>
11	Loop Gain dB20	wave	<input checked="" type="checkbox"/>
12	Output Bias Voltage	900m	<input checked="" type="checkbox"/>
13	I9/Vmid		<input type="checkbox"/>
14	I9/Vup		<input type="checkbox"/>

Plot of Response (350mV)



Analyzing Step Response (350mV)

- 1 Overshoot in $L \rightarrow H$ is result of too much compensation (but it's needed for $H \rightarrow L$).
- 2 Linear decrease in $H \rightarrow L$ can be improved with more compensation (evidently, competing with other transition).

ADE Output (Confirmation of Power, Output Swing)

Outputs			
	Name/Signal/Expr	Value	Plot
1	vreset		<input type="checkbox"/>
2	vout_low2high	1.40119	<input type="checkbox"/>
3	vout_low_180n	201.288m	<input type="checkbox"/>
4	vout_low	200.11m	<input type="checkbox"/>
5	vout_load	wave	<input type="checkbox"/>
6	vout_int		<input type="checkbox"/>
7	vout_high2low	1.39863	<input type="checkbox"/>
8	vout_high_180n	1.6013	<input type="checkbox"/>
9	vout_high	1.59992	<input type="checkbox"/>
10	vout		<input type="checkbox"/>
11	vin_n		<input type="checkbox"/>
12	vin	wave	<input type="checkbox"/>
13	settling_error_low2high	-84.7324m	<input checked="" type="checkbox"/>
14	settling_error_high2low	97.7218m	<input checked="" type="checkbox"/>
15	iavg_1	-26.7447u	<input checked="" type="checkbox"/>
16	power_1	-43.3265u	<input checked="" type="checkbox"/>
17	iavg_1p8	-64.3957u	<input checked="" type="checkbox"/>
18	power_1p8	-115.912u	<input checked="" type="checkbox"/>

Plot of Response (5mV)

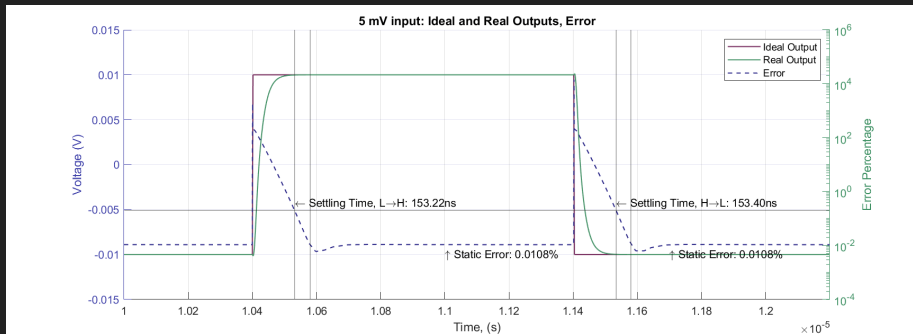


Figure of Merit Calculation

$$\begin{aligned} \text{FOM} &= \frac{10^{-9}}{t_{\text{settle}} \cdot P_{\text{tot}}} \\ &= \frac{10^{-9}}{178.57\text{ns} \cdot 159.24\mu\text{W}} \\ &= 35.167 \end{aligned}$$

Full Changelog (important ones bolded)

Result of Changes (made since submission of report): FOM increased from 26.09 to 35.17.

- 1 Decrease Stage 1 Current** (less power)
- 2 Increase Stage 1 lengths** (higher gain, lower static error allowed higher dynamic error)
- 3 Tune bias voltages using mirror-network parameters.
- 4 Decrease stage 2 length** (increase power consumption but improve transient response)
- 5 Decrease compensation to account for other changes.

Possible Points of Optimization

- 1 Individualized NMOS input vs NMOS vs PMOS Stage 1 lengths (mostly same now).
- 2 Replace compensation resistor with triode transistor (for area + PVT matching).
- 3 Improved class AB implementation (current injector? IEEE Hogervorst paper? Mehta's Improved Hogervorst design from JSSC '19?)
- 4 Explore cascode compensation
- 5 Decrease bias currents more.

Acknowledgments

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The End! Questions?